

# MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

## Digital Transistors (BRT) R1 = 100 kΩ, R2 = 100 kΩ

### NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

| Rating                         | Symbol               | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage         | V <sub>CBO</sub>     | 50  | Vdc  |
| Collector-Emitter Voltage      | V <sub>CEO</sub>     | 50  | Vdc  |
| Collector Current - Continuous | I <sub>C</sub>       | 100 | mAdc |
| Input Forward Voltage          | V <sub>IN(fwd)</sub> | 40  | Vdc  |
| Input Reverse Voltage          | V <sub>IN(rev)</sub> | 10  | Vdc  |

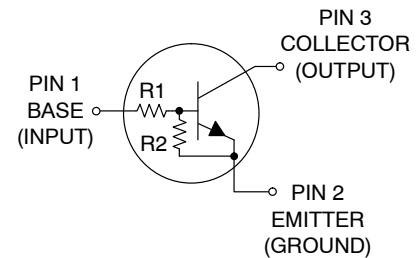
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



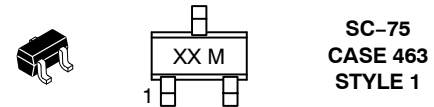
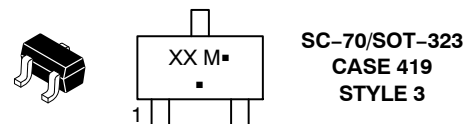
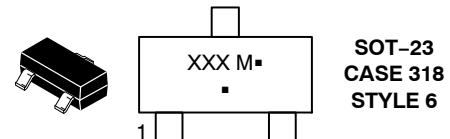
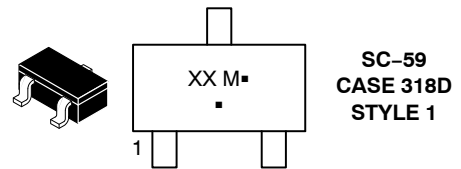
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#### PIN CONNECTIONS



#### MARKING DIAGRAMS



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

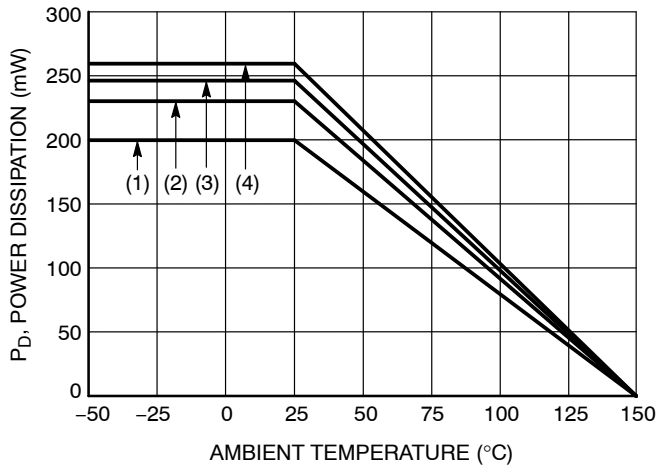
# MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

**Table 1. ORDERING INFORMATION**

| Device                         | Part Marking | Package                    | Shipping†          |
|--------------------------------|--------------|----------------------------|--------------------|
| MUN2236T1G, NSVMUN2236T1G*     | 8N           | SC-59<br>(Pb-Free)         | 3000 / Tape & Reel |
| MMUN2236LT1G, NSVMMUN2236LT1G* | AA5          | SOT-23<br>(Pb-Free)        | 3000 / Tape & Reel |
| MUN5236T1G, NSVMUN5236T1G*     | 8N           | SC-70/SOT-323<br>(Pb-Free) | 3000 / Tape & Reel |
| DTC115EET1G                    | 8N           | SC-75<br>(Pb-Free)         | 3000 / Tape & Reel |
| DTC115EM3T5G                   | 8N           | SOT-723<br>(Pb-Free)       | 8000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-723; Minimum Pad

**Figure 1. Derating Curve**

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

Table 2. THERMAL CHARACTERISTICS

| Characteristic  | Symbol                                       | Max                               | Unit        |
|---|--|-----------------------------------|-------------|
| <b>THERMAL CHARACTERISTICS (SC-59) (MUN2236)</b>  |  |                                   |             |
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | $P_D$<br>230<br>338<br>1.8<br>2.7 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient  | (Note 1)<br>(Note 2)                         | $R_{\theta JA}$<br>540<br>370     | °C/W        |
| Thermal Resistance,<br>Junction to Lead   | (Note 1)<br>(Note 2)                         | $R_{\theta JL}$<br>264<br>287     | °C/W        |
| Junction and Storage Temperature Range  | $T_J, T_{stg}$                               | -55 to +150                       | °C          |

**THERMAL CHARACTERISTICS (SOT-23) (MMUN2236L)**

|   |  |                                   |             |
|---|--|-----------------------------------|-------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | $P_D$<br>246<br>400<br>2.0<br>3.2 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient  | (Note 1)<br>(Note 2)                         | $R_{\theta JA}$<br>508<br>311     | °C/W        |
| Thermal Resistance,<br>Junction to Lead   | (Note 1)<br>(Note 2)                         | $R_{\theta JL}$<br>174<br>208     | °C/W        |
| Junction and Storage Temperature Range  | $T_J, T_{stg}$                               | -55 to +150                       | °C          |

**THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5236)**

|   |  |                                   |             |
|---|--|-----------------------------------|-------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | $P_D$<br>202<br>310<br>1.6<br>2.5 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient  | (Note 1)<br>(Note 2)                         | $R_{\theta JA}$<br>618<br>403     | °C/W        |
| Thermal Resistance,<br>Junction to Lead   | (Note 1)<br>(Note 2)                         | $R_{\theta JL}$<br>280<br>332     | °C/W        |
| Junction and Storage Temperature Range  | $T_J, T_{stg}$                               | -55 to +150                       | °C          |

**THERMAL CHARACTERISTICS (SC-75) (DTC115EE)**

|   |  |                                   |             |
|---|--|-----------------------------------|-------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | $P_D$<br>200<br>300<br>1.6<br>2.4 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient  | (Note 1)<br>(Note 2)                         | $R_{\theta JA}$<br>600<br>400     | °C/W        |
| Junction and Storage Temperature Range  | $T_J, T_{stg}$                               | -55 to +150                       | °C          |

**THERMAL CHARACTERISTICS (SOT-723) (DTC115EM3)**

|   |  |                                   |             |
|---|--|-----------------------------------|-------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | $P_D$<br>260<br>600<br>2.0<br>4.8 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient  | (Note 1)<br>(Note 2)                         | $R_{\theta JA}$<br>480<br>205     | °C/W        |
| Junction and Storage Temperature Range  | $T_J, T_{stg}$                               | -55 to +150                       | °C          |

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.

# MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

**Table 3. ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

| Characteristic   | Symbol        | Min | Typ | Max  | Unit             |
|--|---------------|-----|-----|------|------------------|
| <b>OFF CHARACTERISTICS</b>   |               |     |     |      |                  |
| Collector–Base Cutoff Current<br>( $V_{CB} = 50\text{ V}$ , $I_E = 0$ )                                  | $I_{CBO}$     | –   | –   | 100  | nAdc             |
| Collector–Emitter Cutoff Current<br>( $V_{CE} = 50\text{ V}$ , $I_B = 0$ )                               | $I_{CEO}$     | –   | –   | 500  | nAdc             |
| Emitter–Base Cutoff Current<br>( $V_{EB} = 6.0\text{ V}$ , $I_C = 0$ )                                   | $I_{EBO}$     | –   | –   | 0.05 | mAdc             |
| Collector–Base Breakdown Voltage<br>( $I_C = 10\ \mu\text{A}$ , $I_E = 0$ )                              | $V_{(BR)CBO}$ | 50  | –   | –    | Vdc              |
| Collector–Emitter Breakdown Voltage (Note 3)<br>( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )                    | $V_{(BR)CEO}$ | 50  | –   | –    | Vdc              |
| <b>ON CHARACTERISTICS</b>  |               |     |     |      |                  |
| DC Current Gain (Note 3)<br>( $I_C = 5.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ )                           | $h_{FE}$      | 80  | 150 | –    |                  |
| Collector–Emitter Saturation Voltage (Note 3)<br>( $I_C = 10\text{ mA}$ , $I_B = 0.3\text{ mA}$ )        | $V_{CE(sat)}$ | –   | –   | 0.25 | Vdc              |
| Input Voltage (off)<br>( $V_{CE} = 5.0\text{ V}$ , $I_C = 100\ \mu\text{A}$ )                            | $V_{i(off)}$  | –   | 1.2 | 0.5  | Vdc              |
| Input Voltage (on)<br>( $V_{CE} = 0.3\text{ V}$ , $I_C = 1.0\text{ mA}$ )                                | $V_{i(on)}$   | 3.0 | 1.7 | –    | Vdc              |
| Output Voltage (on)<br>( $V_{CC} = 5.0\text{ V}$ , $V_B = 5.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )   | $V_{OL}$      | –   | –   | 0.2  | Vdc              |
| Output Voltage (off)<br>( $V_{CC} = 5.0\text{ V}$ , $V_B = 0.25\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ ) | $V_{OH}$      | 4.9 | –   | –    | Vdc              |
| Input Resistor   | $R_1$         | 70  | 100 | 130  | $\text{k}\Omega$ |
| Resistor Ratio   | $R_1/R_2$     | 0.8 | 1.0 | 1.2  |                  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .

TYPICAL CHARACTERISTICS  
 MUN2236, MMUN2236L, MUN5236, NSVMUN5236, DTC115EE, DTC115EM3

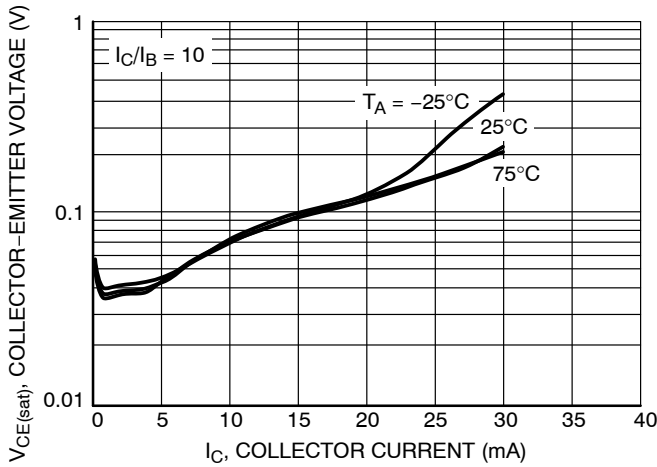


Figure 2.  $V_{CE(sat)}$  versus  $I_C$

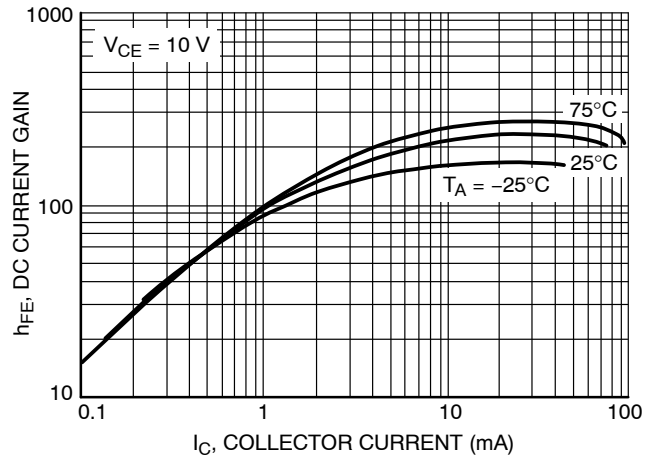


Figure 3. DC Current Gain

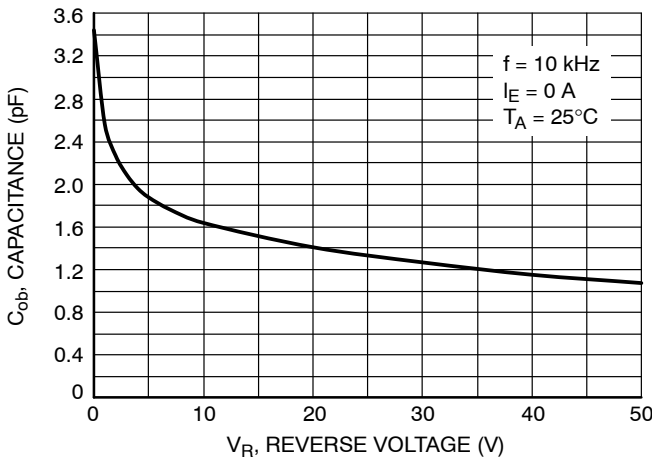


Figure 4. Output Capacitance

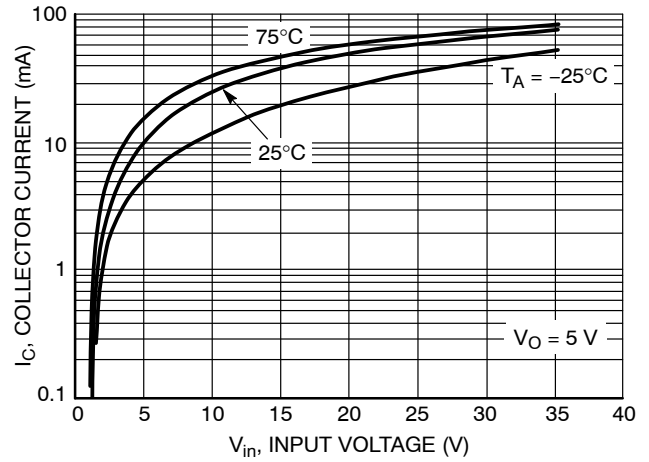


Figure 5. Output Current versus Input Voltage

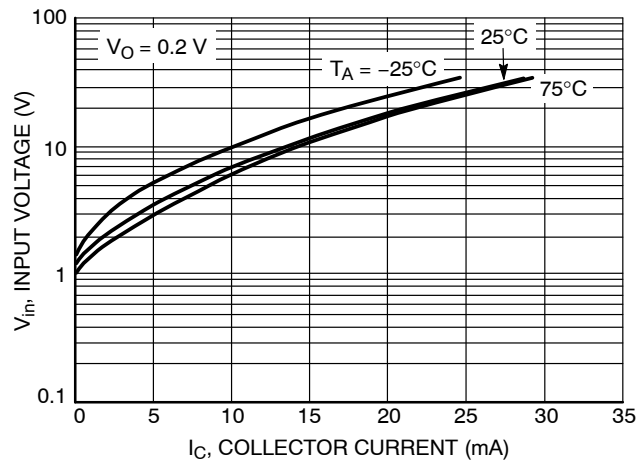


Figure 6. Input Voltage versus Output Current

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)**  
CASE 318  
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM            | MILLIMETERS |      |      | INCHES |       |       |
|----------------|-------------|------|------|--------|-------|-------|
|                | MIN.        | NOM. | MAX. | MIN.   | NOM.  | MAX.  |
| A              | 0.89        | 1.00 | 1.11 | 0.035  | 0.039 | 0.044 |
| A1             | 0.01        | 0.06 | 0.10 | 0.000  | 0.002 | 0.004 |
| b              | 0.37        | 0.44 | 0.50 | 0.015  | 0.017 | 0.020 |
| c              | 0.08        | 0.14 | 0.20 | 0.003  | 0.006 | 0.008 |
| D              | 2.80        | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| E              | 1.20        | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| e              | 1.78        | 1.90 | 2.04 | 0.070  | 0.075 | 0.080 |
| L              | 0.30        | 0.43 | 0.55 | 0.012  | 0.017 | 0.022 |
| L1             | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.027 |
| H <sub>E</sub> | 2.10        | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| T              | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

|                         |                        |  |
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| <b>DESCRIPTION:</b>     | <b>SOT-23 (TO-236)</b> | <b>PAGE 1 OF 2</b>   |

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**MECHANICAL CASE OUTLINE  
PACKAGE DIMENSIONS**



**SOT-23 (TO-236)  
CASE 318  
ISSUE AT**

DATE 01 MAR 2023

- |   |   |   |   |   |   |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:<br>CANCELLED                            | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE  |   |   |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE      | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE     | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          |
| STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE      | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE | STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE          |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN       | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT   | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE           | STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION |
| STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE     |   |   |   |   |

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| <b>DESCRIPTION:</b>     | <b>SOT-23 (TO-236)</b> | <b>PAGE 2 OF 2</b>  |

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SC-59  
CASE 318D-04  
ISSUE H

DATE 28 JUN 2012

SCALE 2:1



### SOLDERING FOOTPRINT\*



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

| DIM | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A   | 1.00        | 1.15 | 1.30 | 0.039  | 0.045 | 0.051 |
| A1  | 0.01        | 0.06 | 0.10 | 0.001  | 0.002 | 0.004 |
| b   | 0.35        | 0.43 | 0.50 | 0.014  | 0.017 | 0.020 |
| c   | 0.09        | 0.14 | 0.18 | 0.003  | 0.005 | 0.007 |
| D   | 2.70        | 2.90 | 3.10 | 0.106  | 0.114 | 0.122 |
| E   | 1.30        | 1.50 | 1.70 | 0.051  | 0.059 | 0.067 |
| e   | 1.70        | 1.90 | 2.10 | 0.067  | 0.075 | 0.083 |
| L   | 0.20        | 0.40 | 0.60 | 0.008  | 0.016 | 0.024 |
| HE  | 2.50        | 2.80 | 3.00 | 0.099  | 0.110 | 0.118 |

### GENERIC MARKING DIAGRAM



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package\*

(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |  |
|---|---|--|
| STYLE 1:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE |
|---|---|--|

- |   |  |  |
|---|--|--|
| STYLE 4:<br>PIN 1. CATHODE<br>2. N.C.<br>3. ANODE | STYLE 5:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 6:<br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE/CATHODE |
|---|--|--|

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

## SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

| DIM            | MILLIMETERS |      |      | INCHES    |       |       |
|----------------|-------------|------|------|-----------|-------|-------|
|                | MIN.        | NOM. | MAX. | MIN.      | NOM.  | MAX.  |
| A              | 0.80        | 0.90 | 1.00 | 0.032     | 0.035 | 0.040 |
| A1             | 0.00        | 0.05 | 0.10 | 0.000     | 0.002 | 0.004 |
| A2             | 0.70 REF    |      |      | 0.028 BSC |       |       |
| b              | 0.30        | 0.35 | 0.40 | 0.012     | 0.014 | 0.016 |
| c              | 0.10        | 0.18 | 0.25 | 0.004     | 0.007 | 0.010 |
| D              | 1.80        | 2.00 | 2.20 | 0.071     | 0.080 | 0.087 |
| E              | 1.15        | 1.24 | 1.35 | 0.045     | 0.049 | 0.053 |
| e              | 1.20        | 1.30 | 1.40 | 0.047     | 0.051 | 0.055 |
| e1             | 0.65 BSC    |      |      | 0.026 BSC |       |       |
| L              | 0.20        | 0.38 | 0.56 | 0.008     | 0.015 | 0.022 |
| H <sub>E</sub> | 2.00        | 2.10 | 2.40 | 0.079     | 0.083 | 0.095 |

### GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

### SOLDERING FOOTPRINT

|   |   |   |  |   |
|---|---|---|--|---|
| STYLE 1:<br>CANCELLED                                 | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE     | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          |
| STYLE 6:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 7:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 8:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN      | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. ANODE-CATHODE |
|   |   |   |  | STYLE 11:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     |

|                         |                        |  |
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SC-75/SOT-416**  
CASE 463-01  
ISSUE G

DATE 07 AUG 2015

SCALE 4:1



STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

| DIM | MILLIMETERS |      |      | INCHES   |       |       |
|-----|-------------|------|------|----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN      | NOM   | MAX   |
| A   | 0.70        | 0.80 | 0.90 | 0.027    | 0.031 | 0.035 |
| A1  | 0.00        | 0.05 | 0.10 | 0.000    | 0.002 | 0.004 |
| b   | 0.15        | 0.20 | 0.30 | 0.006    | 0.008 | 0.012 |
| C   | 0.10        | 0.15 | 0.25 | 0.004    | 0.006 | 0.010 |
| D   | 1.55        | 1.60 | 1.65 | 0.061    | 0.063 | 0.065 |
| E   | 0.70        | 0.80 | 0.90 | 0.027    | 0.031 | 0.035 |
| e   | 1.00 BSC    |      |      | 0.04 BSC |       |       |
| L   | 0.10        | 0.15 | 0.20 | 0.004    | 0.006 | 0.008 |
| HE  | 1.50        | 1.60 | 1.70 | 0.060    | 0.063 | 0.067 |

### GENERIC MARKING DIAGRAM\*



- XX = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

### SOLDERING FOOTPRINT\*



SCALE 10:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

|                         |                      |  |
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

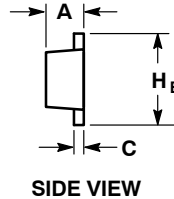
ON Semiconductor®



SCALE 4:1

**SOT-723**  
CASE 631AA-01  
ISSUE D

DATE 10 AUG 2009

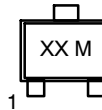


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

| MILLIMETERS |          |      |      |
|-------------|----------|------|------|
| DIM         | MIN      | NOM  | MAX  |
| A           | 0.45     | 0.50 | 0.55 |
| b           | 0.15     | 0.21 | 0.27 |
| b1          | 0.25     | 0.31 | 0.37 |
| C           | 0.07     | 0.12 | 0.17 |
| D           | 1.15     | 1.20 | 1.25 |
| E           | 0.75     | 0.80 | 0.85 |
| e           | 0.40 BSC |      |      |
| H E         | 1.15     | 1.20 | 1.25 |
| L           | 0.29 REF |      |      |
| L2          | 0.15     | 0.20 | 0.25 |

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code

- |   |  |  |  |  |
|---|--|--|--|--|
| STYLE 1:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 2:<br>PIN 1. ANODE<br>2. N/C<br>3. CATHODE | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 5:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN |
|---|--|--|--|--|

**RECOMMENDED SOLDERING FOOTPRINT\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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